

STB11NM60FD - STB11NM60FD-1 STP11NM60FD - STP11NM60FDFP

N-channel 600V - 0.40Ω - 11A - TO-220/TO-220FP/D²PAK/I²PAK FDmesh™ Power MOSFET (with fast diode)

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STB11NM60FD	600V	<0.45Ω	11A
STB11NM60FD-1	600V	<0.45Ω	11A
STP11NM60FD	600V	<0.45Ω	11A
STP11NM60FDFP	600V	<0.45Ω	11A

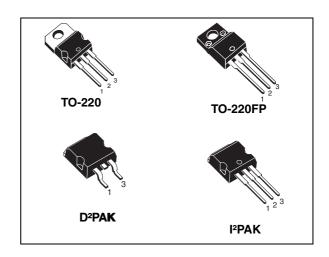
- 100% avalanche tested
- High dv/dt and avalanche capabilities
- Low input capacitance and gate charge
- Low gate input resistance
- Tight process control and high manufacturing yields

Description

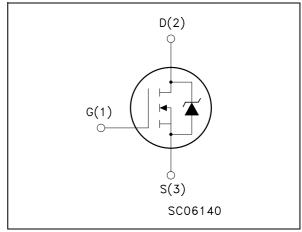
The FDmesh™ associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STB11NM60FD	STB11NM60FD B11NM60FD		Tape & reel
STB11NM60FD-1	B11NM60FD	I ² PAK	Tube
STP11NM60FD	STP11NM60FD P11NM60FD		Tube
STP11NM60FDFP	P11NM60FDFP	TO-220FP	Tube

July 2006 Rev 9 1/17

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1 Electrical ratings

Table 1. Absolute maximum ratings

		Val	ue	Unit
Symbol	Parameter	TO-220/ D²PAK/l²PAK	TO-220FP	
V _{DS}	Drain-source voltage (v _{gs} = 0)	60	0	V
V_{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	60	0	٧
V _{GS}	Gate- source voltage	±3	٧	
I _D	Drain current (continuos) at T _C = 25°C	11 11 (1)		Α
I _D	Drain current (continuos) at T _C = 100°C	7	7 ⁽¹⁾	Α
I _{DM} ⁽²⁾	Drain current (pulsed)	44	44 ⁽¹⁾	Α
P _{TOT}	Total dissipation at T _C = 25°C	160	35	W
	Derating factor	0.88	0.28	W/°C
dv/dt (3)	Peak diode recovery voltage slope	20		V/ns
V _{ISO}	Insulation winthstand voltage (dc)	2500		V
T _{stg}	Storage temperature	–65 to	°C	

- 1. Limited only by maximum temperature allowed
- 2. Pulse width limited by safe operating area
- 3. I_{SD} <11A, di/dt<400A/ μ s, V_{DD} = 80% $V_{(BR)DSS}$

Table 2. Thermal resistance

		Val		
Symbol	Parameter	TO-220 D²PAK/I²PAK	TO-220FP	Unit
R _{thj-case}	Thermal resistance junction-case Max	0.78 3.57		°C/W
R _{thj-a}	Thermal resistance junction-ambient Max	62.5		°C/W
T _I	Maximum lead temperature for soldering purpose	300		°C

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	5.5	Α
E _{AS}	Single pulse avalanche energy (starting Tj = 25°C, $I_D = I_{AR}$, $V_{DD} = 35V$)	350	mJ

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions		Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \ \mu A, \ V_{GS} = 0$	600			٧
1	Zero gate voltage	V _{DS} = Max rating			1	μΑ
I _{DSS}	Drain current (V _{GS} = 0)	V _{DS} =Max rating, T _C =125°C			100	μΑ
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	$V_{GS} = \pm 30V$			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3	4	5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10V, I _D = 5.5A		0.40	0.45	W

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 5.5A$		5.2		S
C _{iss}	Input capacitance			900		pF
C _{oss}	Output capacitance	$V_{DS} = 25V, f = 1 \text{ MHz},$		350		pF
C _{rss}	Reverse transfer capacitance	$V_{GS} = 0$		35		pF
C _{oss eq} (2)	Equivalent output capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to}$ 400V		100		pF
R_{G}	Gate input resistance	f=1 MHz Gate DC Bias= 0 test signal level = 20mV open drain		3		Ω
Q_g	Total gate charge	V _{DD} = 400V, I _D = 11A,		28	40	nC
Q_{gs}	Gate-source charge	V _{GS} = 10V		7.8		nC
Q_{gd}	Gate-drain charge	(see Figure 15)		13		nC

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

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^{2.} $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)} t _r	Turn-on delay time Rise time	V_{DD} = 250V, I_D = 5.5A R_G = 4.7 Ω V_{GS} = 10V (see Figure 14)		20 16		ns ns
t _{r(Voff)} t _f t _c	Off-voltage rise time Fall time Cross-over time	$V_{DD} = 400V, I_{D} = 11A,$ $R_{G} = 4.7\Omega, V_{GS} = 10V$ (see Figure 16)		10 15 24		ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				11	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				44	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 11A, V _{GS} = 0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 11A, V_{DD} = 50V di/dt = 100A/µs, (see Figure 19)		140 680 A		ns nC A
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 11A, V_{DD} = 50V di/dt = 100A/ μ s, Tj=150°C (see Figure 19)		260 1600 13		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

Electrical characteristics (curves) 2.1

Figure 1. Safe operating area

Figure 2. Thermal impedance

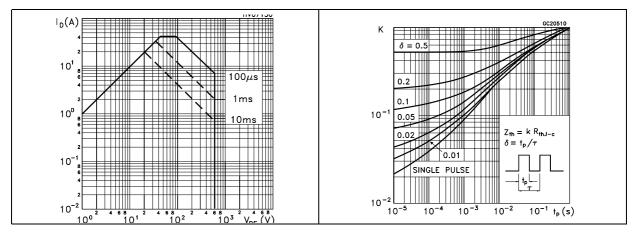


Figure 3. Safe operating areafor TO-220FP

Figure 4. Thermal impedance for TO-220FP

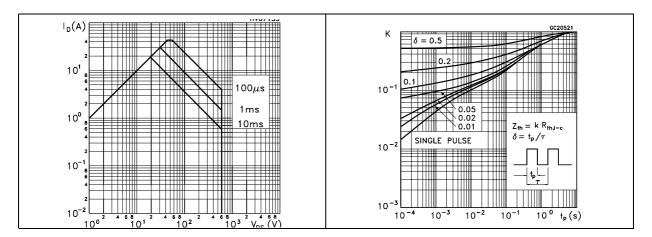
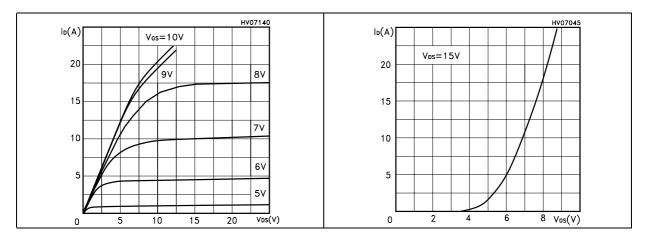


Figure 5. **Output characterisics**

Figure 6. **Transfer characteristics**



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Figure 7. Transconductance

Figure 8. Static drain-source on resistance

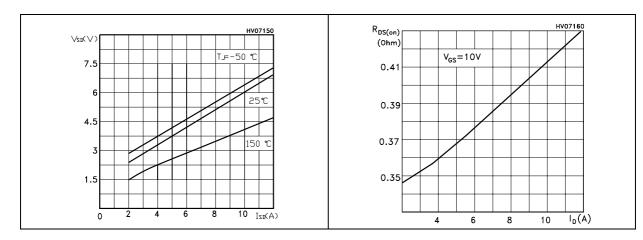


Figure 9. Gate charge vs gate-source voltage Figure 10. Capacitance variations

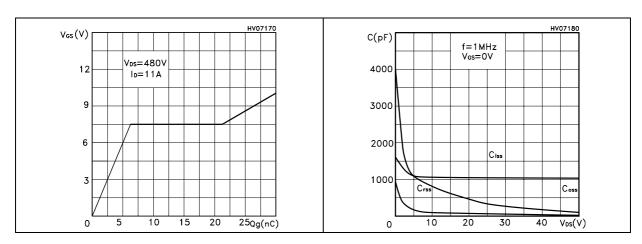


Figure 11. Normalized gate threshold voltage Figure 12. Normalized on resistance vs vs temperature temperature

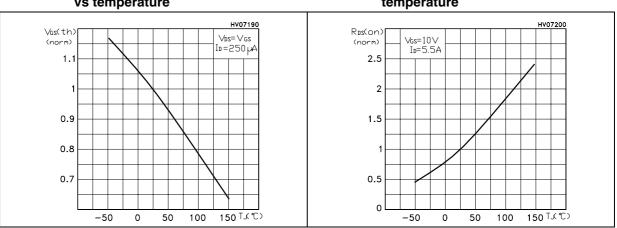
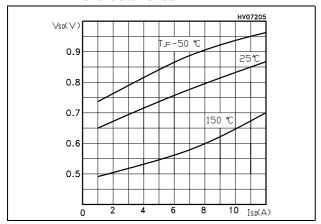


Figure 13. Source-drain diode forward characteristics



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3 Test circuit

Figure 14. Switching times test circuit for resistive load

Figure 15. Gate charge test circuit

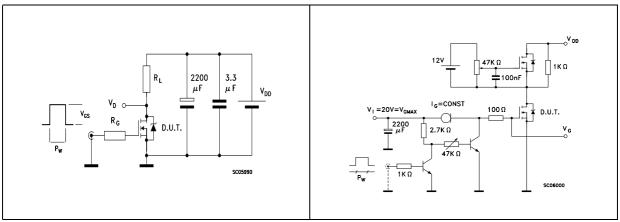


Figure 16. Test circuit for inductive load switching and diode recovery times

Figure 17. Unclamped Inductive load test circuit

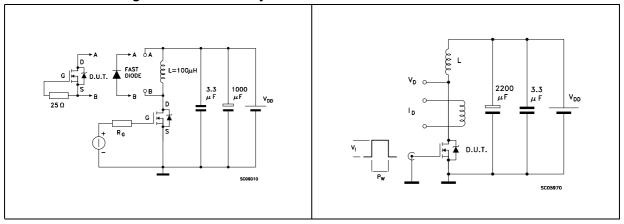
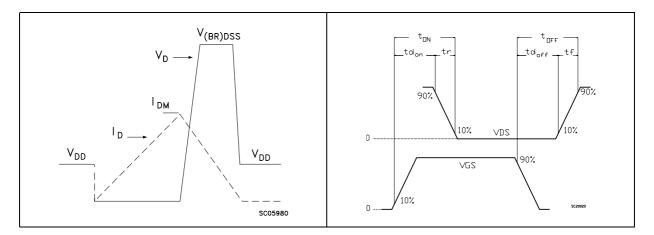


Figure 18. Unclamped inductive waveform

Figure 19. Switching time waveform

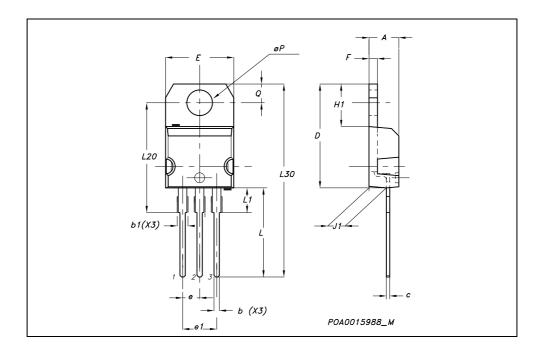


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

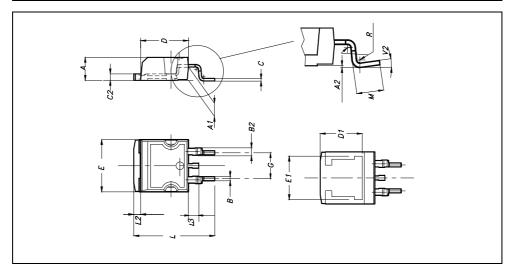
TO-220 MECHANICAL DATA

DIM.		mm.			inch	
DIN.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



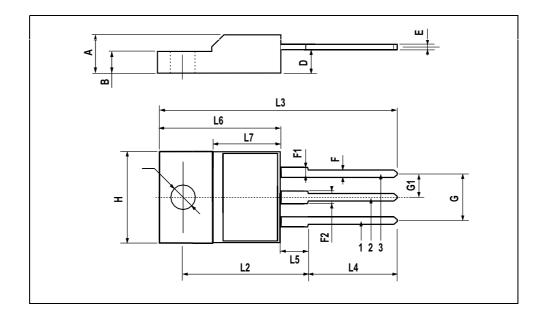
D²PAK MECHANICAL DATA

DIM.		mm.			inch	
DIN.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0 _δ		4º			



TO-220FP MECHANICAL DATA

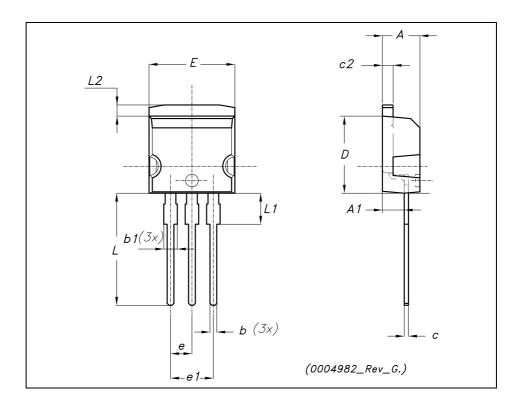
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
Е	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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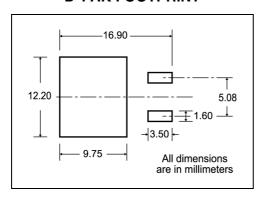
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
С	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
Е	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055

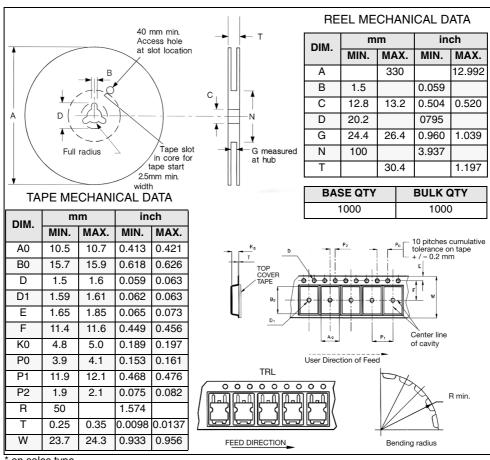


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 8. Revision history

Date	Revision	Changes	
09-Sep-2004	6	Preliminary version	
08-May-2006	7	D ² PAK package inserted	
22-May-2006	8	Updated values Table 5: Dynamic	
26-Jul-2006	9	New template, no content change	

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